

Tomohiko Shibata

List of Publications by Year in descending order

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291
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth of high-quality GaN films on epitaxial AlN/sapphire templates by MOVPE. Journal of Crystal Growth, 2002, 244, 6-11.	1.5	52
2	AlN epitaxial growth on off-angle R-plane sapphire substrates by MOCVD. Journal of Crystal Growth, 2001, 229, 63-68.	1.5	41
3	Transmission Electron Microscopic Observation of $\text{AlN}/\alpha\text{-Al}_2\text{O}_3$ Heteroepitaxial Interface with Initial-Nitriding AlN Layer. Japanese Journal of Applied Physics, 1995, 34, L760-L763.	1.5	38
4	Growth of Thick AlN Layer by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2005, 44, L505-L507.	1.5	37
5	AlGaIn-Based Deep Ultraviolet Light-Emitting Diodes Grown on Epitaxial AlN/Sapphire Templates. Japanese Journal of Applied Physics, 2008, 47, 43-46.	1.5	33
6	Growth and characterization of AlInN on AlN template. Journal of Crystal Growth, 2004, 272, 381-385.	1.5	32
7	Nanostructural characterization and two-dimensional electron-gas properties in high-mobility AlGaIn/AlN/GaN heterostructures grown on epitaxial AlN/sapphire templates. Journal of Applied Physics, 2005, 98, 063713.	2.5	32
8	DC Characteristics in High-Quality AlGaIn/AlN/GaN High-Electron-Mobility Transistors Grown on AlN/Sapphire Templates. Japanese Journal of Applied Physics, 2005, 44, 6490-6494.	1.5	29
9	Suppression of Crack Generation Using High-Compressive-Strain AlN/Sapphire Template for Hydride Vapor Phase Epitaxy of Thick AlN Film. Japanese Journal of Applied Physics, 2007, 46, L552-L555.	1.5	16
10	Influence of growth interruption and Si doping on the structural and optical properties of Al _x GaN/AlN (x>0.5) multiple quantum wells. Journal of Crystal Growth, 2007, 298, 500-503.	1.5	15
11	Characterization of high-quality epitaxial AlN films grown by MOVPE. Materials Research Society Symposia Proceedings, 2001, 693, 774.	0.1	5
12	Fabrication of thick AlN film by low pressure hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1479-1482.	0.8	5
13	Structural and optical properties of Si-doped AlGaIn/AlN multiple quantum wells grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2494-2497.	0.8	0